



40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 4)
40V	7.6 m Ω @ V _{GS} = 10V	100A

Description

This new generation n-channel enhancement mode MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switches.

Applications

- Power management
- DC-DC converters
- Motor controls

Features

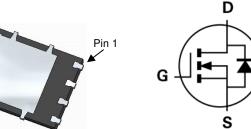
- Rated to +175°C Ideal for High Ambient Temperature Environments
- Thermally Efficient Package-Cooler Running Applications
- High-Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- < 1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 - https://www.diodes.com/quality/product-definitions/
- An automotive-compliant part is available under separate datasheet (<u>DMTH4007SPSQ</u>)

Mechanical Data

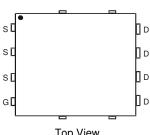
- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



Top View



Internal Schematic



Top View Pin Configuration

Site 2:

PowerDI5060-8/SWP (Type UX)

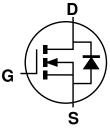


Top View

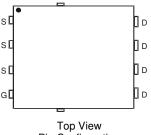


Bottom View

Bottom View



Internal Schematic



chematic Pin Configuration

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Package limited.



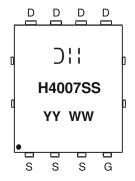
Ordering Information (Note 5)

Part Number	Package	Packing		
Part Number	Fackage	Qty.	Carrier	
DMTH4007SPS-13	PowerDI5060-8	2,500	Tape & Reel	
DIVITH400/3F3-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

Note:

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





H4007SS = Product Type Marking Code
YYWW = Date Code Marking
YY or YY = Last Two Digits of Year (ex: 23 = 2023) WW = Week Code (01 to 53)

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	40	V	
Gate-Source Voltage		Vgss	±20	V	
Continuous Drain Current (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	15.7 13.1	А	
Continuous Drain Current (Note 7)	T _C = +25°C (Note 4)	ID	100	Α	
	$T_{C} = +100^{\circ}C$		77	1	
Maximum Continuous Body Diode Forward Current (Note 7)		Is	100	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		Ірм	200	Α	
Avalanche Current, L = 0.3mH		las	20	Α	
Avalanche Energy, L = 0.3mH		Eas	60	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)		Reja	53	°C/W
Total Power Dissipation (Note 7)	$T_C = +25^{\circ}C$	P _D	136	W
Thermal Resistance, Junction to Case (Note 7)		Rejc	1.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate. 7. Thermal resistance from junction to soldering point (on the exposed drain pad). Notes:



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

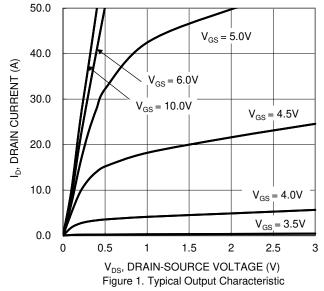
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	1	_	٧	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	1	1	1	μΑ	$V_{DS} = 32V$, $V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	-	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	4.9	7.6	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	2,082	_		$V_{DS} = 25V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	1	790	_	pF		
Reverse Transfer Capacitance	Crss	_	113	_			
Gate Resistance	Rg	_	0.46		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg		41.9			$V_{DS} = 30V$, $I_{D} = 20A$, $V_{GS} = 10V$	
Gate-Source Charge	Qgs		10	_	nC		
Gate-Drain Charge	Qgd		11.5	_			
Turn-On Delay Time	td(ON)		7	_		$\begin{split} V_{DD} &= 30 \text{V, V}_{GS} = 10 \text{V} \\ I_{D} &= 20 \text{A, R}_{g} = 3 \Omega \end{split}$	
Turn-On Rise Time	t _R	_	11.5	_	no		
Turn-Off Delay Time	tD(OFF)		15.6	_	ns		
Turn-Off Fall Time	tF	-	8.8	_			
Body Diode Reverse Recovery Time	trr	_	29.9	_	ns	I= 20A dl/dt 100A/us	
Body Diode Reverse Recovery Charge	Q _{RR}	_	23	_	nC	I _F = 20A, dl/dt = 100A/μs	

Notes:

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







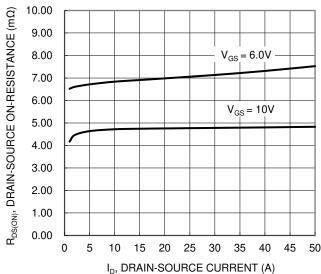


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

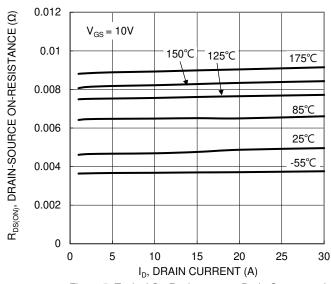


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

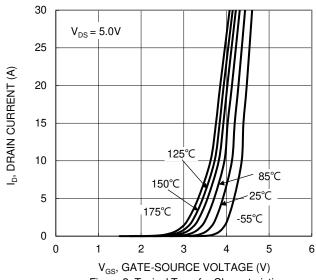
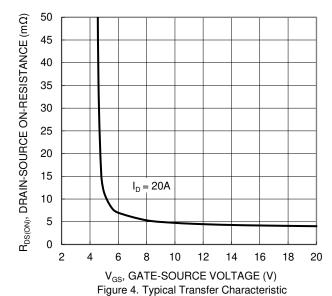


Figure 2. Typical Transfer Characteristic



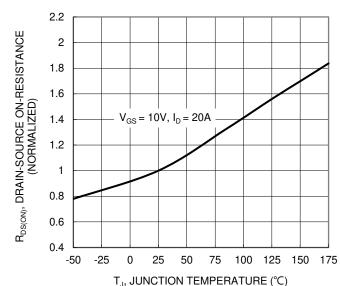


Figure 6. On-Resistance Variation with Temperature

DMTH4007SPS



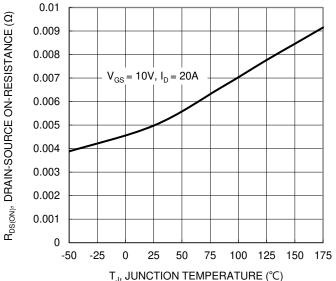
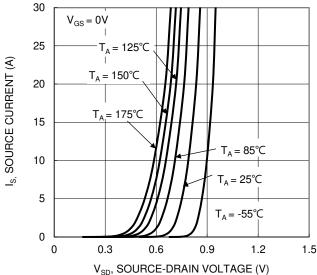
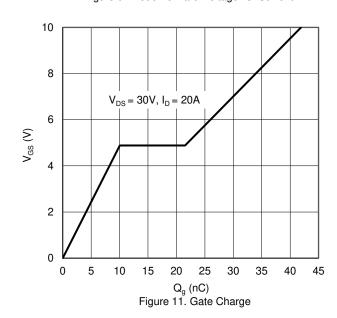


Figure 7. On-Resistance Variation with Temperature

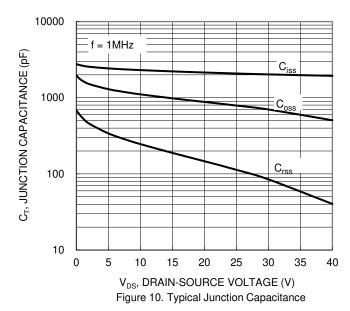


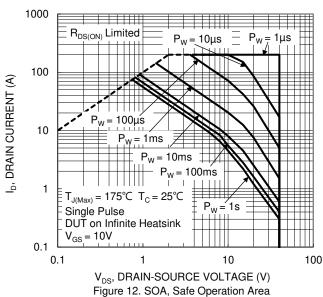
V_{SD}, SOURCE-DRAIN VOLTAGE (V)
Figure 9. Diode Forward Voltage vs. Current



4 $V_{\text{GS(TH)}},$ GATE THRESHOLD VOLTAGE (V) 3.5 3 $I_D = 1mA$ 2.5 2 $I_{D} = 250 \mu A$ 1.5 0.5 -50 -25 25 50 75 100 125 150 175 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Temperature







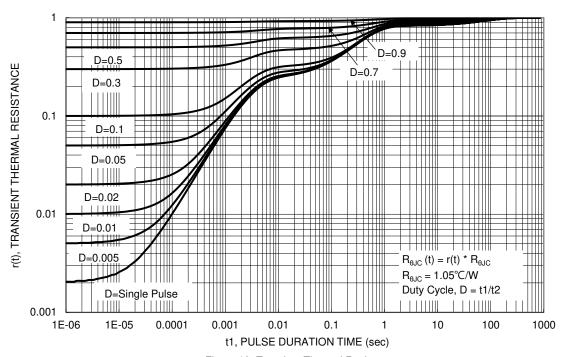


Figure 13. Transient Thermal Resistance

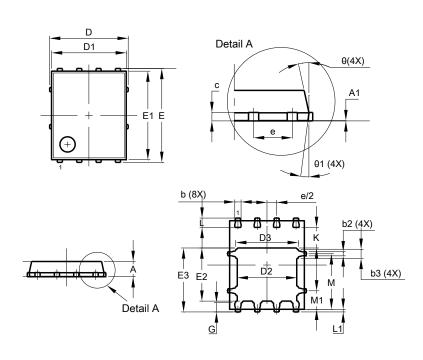


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

PowerDI5060-8

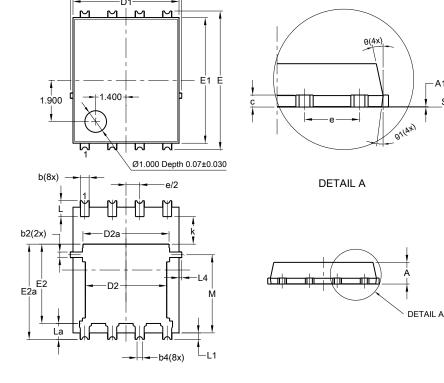


PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A 1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D	ļ	5.15 BSC	;	
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
Е	(6.15 BSC		
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е		1.27 BSC		
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
М	3.235	4.035	3.635	
М1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

Site 2:

PowerDI5060-8/SWP (Type UX)

Seating Plane



PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Тур
Α	0.90	1.10	1.00
A 1	0	0.05	
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	C).25REF	
С	0.230	0.330	0.277
D	5	.15 BS0	\sim
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
Е	6	.40 BS0	
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
е	1.27BSC		
k	1.05	-	
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
М	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

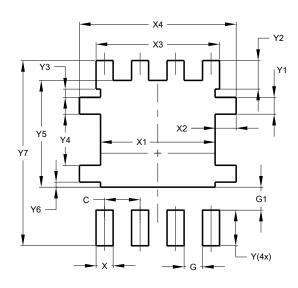


Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

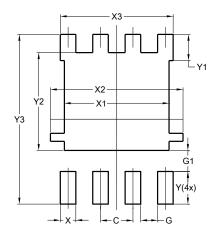
PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y 1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y 7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



Dimensions	Value
Dilliciisions	(in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
Х3	4.420
Υ	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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